

Silicon Photodiodes KPD3065C

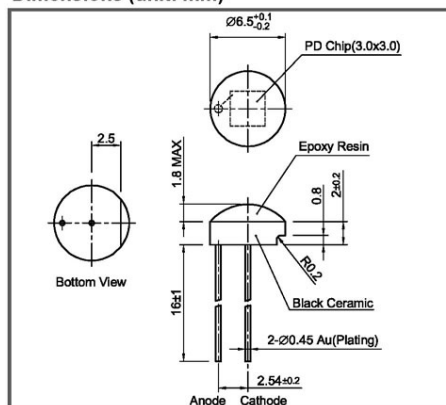
■ Features

- Transparent epoxy potting
- High sensitivity

■ Applications

- Optical switches
- Optical encoders
- Pulse detectors
- Sensors and industrial controls

Dimensions (unit: mm)



■ Specifications

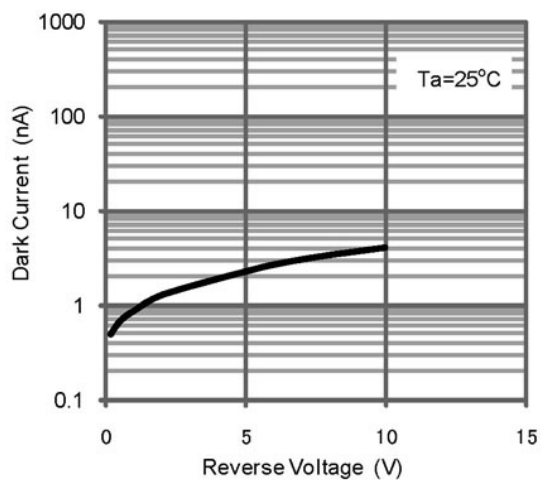
➤ Absolute Maximum Ratings

Parameter	Symbol	Value	Unit	Conditions
Reverse voltage	V_R	10	V	
Reverse Current	I_R	1	mA	
Forward current	I_F	10	mA	
Operating temperature	T_{opr}	-20 to +80	°C	To avoid a dew condensation
Storage temperature	T_{stg}	-20 to +100	°C	To avoid a dew condensation

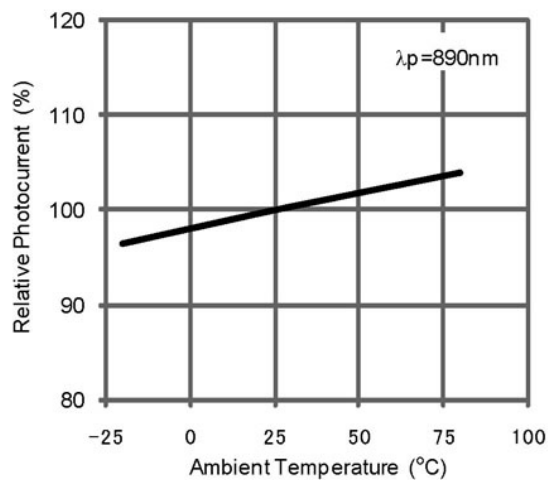
➤ Electrical and Optical characteristics

Parameter	Symbol	Value			Unit	Conditions
		Min.	Typ.	Max		
Sensitive size	S		2.59x2.59		mm	
Operating voltage	V_{opr}			5	V	
Sensitive wavelength	λ	400	950(λ_p)	1000	nm	λ_p =Peak wavelength
Open circuit voltage	V_{op}		350		mV	1000lx @2856k
Short Circuit Current	I_{sh}	60	70	85	μA	1000lx @2856k
Dark current	I_D			30	nA	$V_R=5V$
Terminal capacitance	C_t		17		pF	$V_R=5V, f=1MHz$
Half angle	2θ		120		deg	

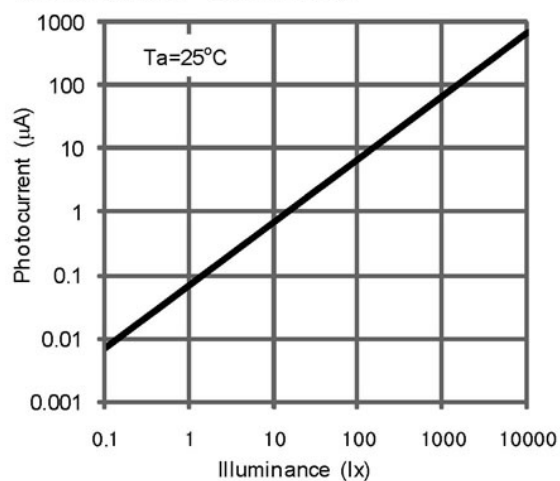
Dark Current - Reverse Voltage



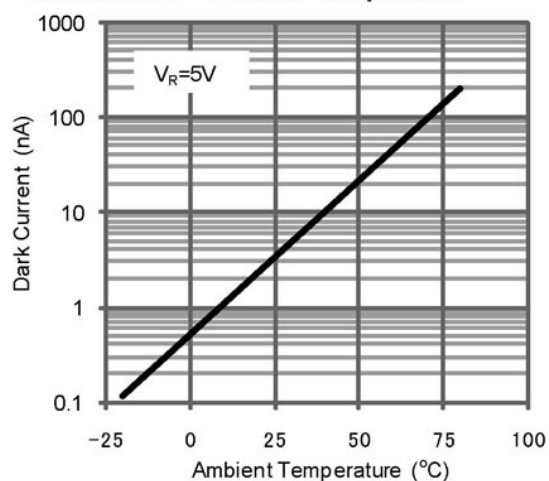
Photocurrent - Ambient Temperature



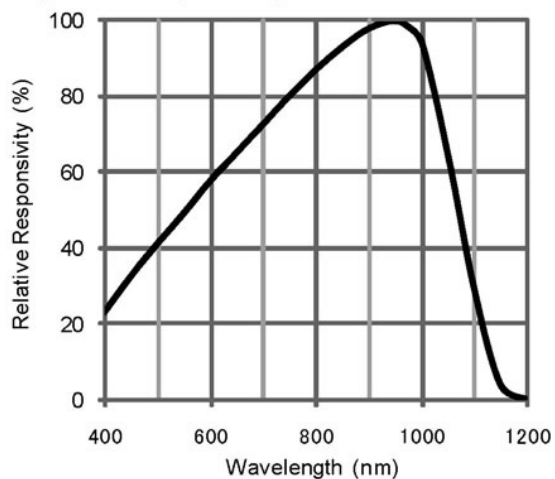
Photocurrent - Illuminance



Dark Current - Ambient Temperature



Spectral Responsivity



Directivity

